

COMPLEMENTARY SILICON POWER DARLINGTON TRANSISTORS

- SGS-THOMSON PREFERRED SALESTYPES
- MONOLITHIC DARLINGTON CONFIGURATION
- COMPLEMENTARY PNP - NPN DEVICES
- INTEGRATED ANTIPARALLEL COLLECTOR-EMITTER DIODE

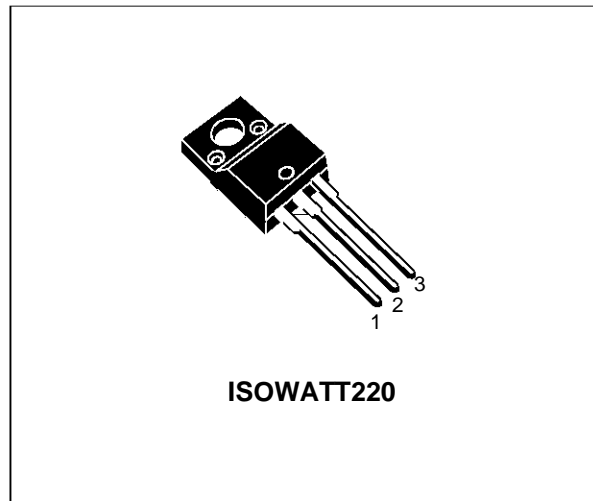
APPLICATIONS

- LINEAR AND SWITCHING INDUSTRIAL EQUIPMENT

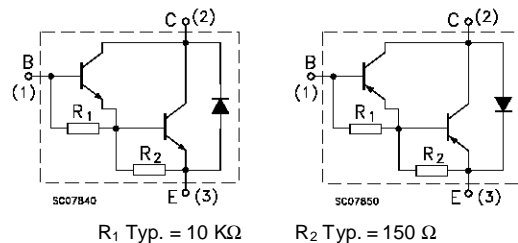
DESCRIPTION

The BDW93CFI, is a silicon epitaxial-base NPN transistor in monolithic Darlington configuration and is mounted in ISOWATT220 plastic package. It is intended for use in power linear and switching applications.

The complementary PNP type is the BDW94CFI.



INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		NPN	BDW93CFI	
		PNP	BDW94CFI	
V_{CBO}	Collector-Base Voltage ($I_E = 0$)		100	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)		100	V
I_C	Collector Current		12	A
I_{CM}	Collector Peak Current		15	A
I_B	Base Current		0.2	A
P_{tot}	Total Dissipation at $T_c \leq 25^\circ C$		40	W
T_{stg}	Storage Temperature		-65 to 150	$^\circ C$
T_j	Max. Operating Junction Temperature		150	$^\circ C$

For PNP types voltage and current values are negative.

BDW93CFI / BDW94CFI

THERMAL DATA

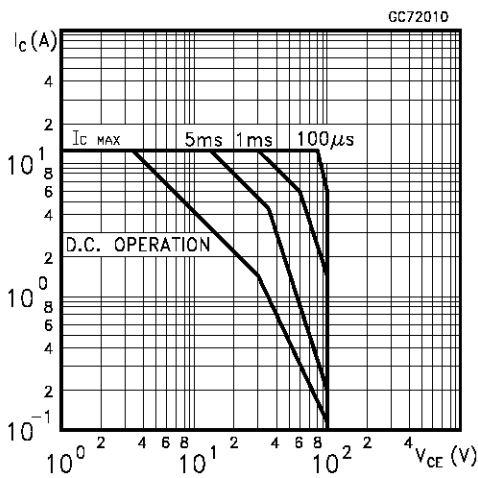
R _{thj-case}	Thermal Resistance Junction-case	3.1	°C/W
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ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CBO}	Collector Cut-off Current (I _E = 0)	V _{CB} = 100 V V _{CB} = 100 V T _{case} = 150 °C			100 5	μA mA
I _{CEO}	Collector Cut-off Current (I _B = 0)	V _{CE} = 80 V			1	mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			2	mA
V _{CEO(sus)*}	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 100 mA	100			V
V _{CE(sat)*}	Collector-Emitter Saturation Voltage	I _C = 5 A I _B = 20 mA I _C = 10 A I _B = 100 mA			2 3	V V
V _{BE(sat)*}	Base-Emitter Saturation Voltage	I _C = 5 A I _B = 20 mA I _C = 10 A I _B = 100 mA			2.5 4	V V
h _{FE*}	DC Current Gain	I _C = 3 A V _{CE} = 3 V I _C = 5 A V _{CE} = 3 V I _C = 10 A V _{CE} = 3 V	1000 750 100		20000	
V _{F*}	Parallel-diode Forward Voltage	I _F = 5 A I _F = 10 A		1.3 1.8	2 4	V V
h _{fe}	Small Signal Current Gain	I _C = 1 A V _{CE} = 10 V f = 1 MHz	20			

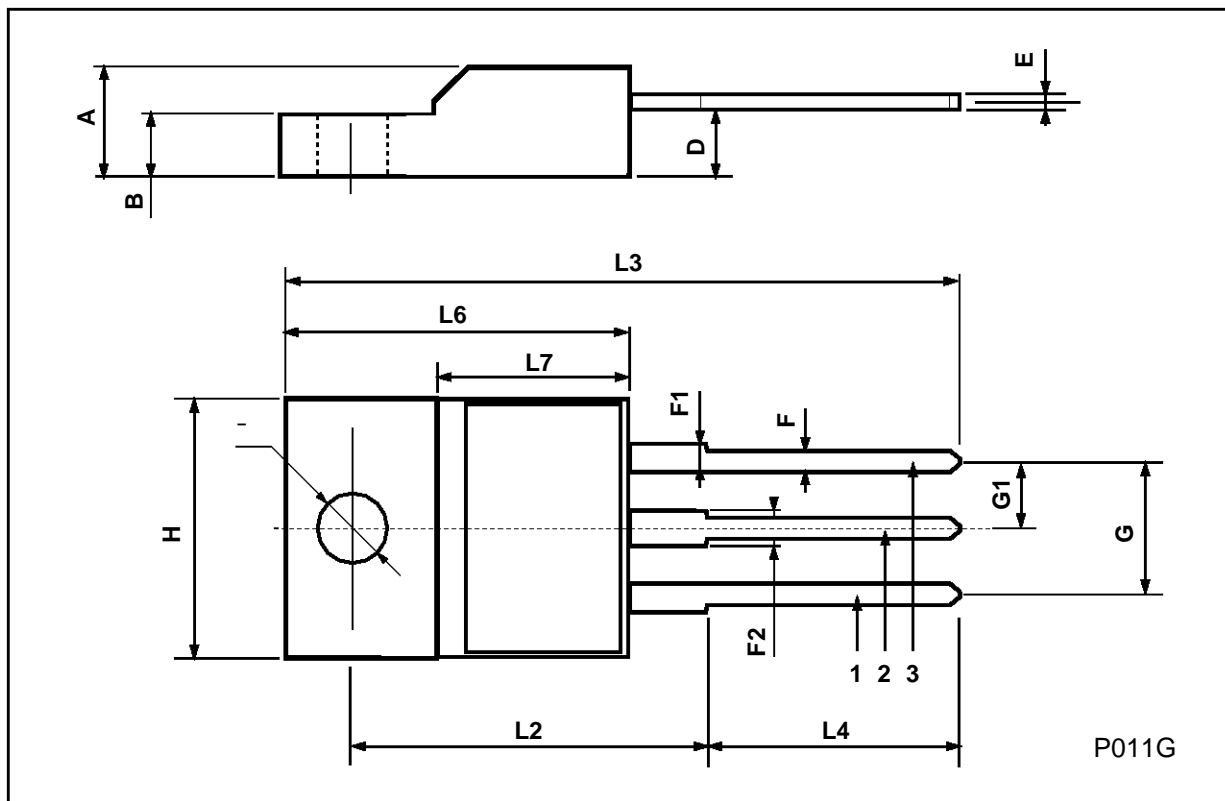
* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %
For PNP types voltage and current values are negative.

Safe Operating Area



ISOWATT220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.4		0.7	0.015		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



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